PTO/SB/084(10-01)
Approved for use through 10/31/2002, ONG 651-0031
US Pased & Tradenerk Office; U.S. DEPARTMENT OF CONDIENCE
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a void ONG control number. Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE 10/634,174 **Application Number** STATEMENT BY APPECAL
(Use as many sheets as negessary) August 5, 2003 Filing Date **First Named Inventor** Forbes, Leonard **Group Art Unit** 2823 Garcia, Joannie **Examiner Name** Attorney Docket No: 1303.102US1 Sheet 1 of 1

		US P	ATENT DOCUMENTS	
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
JAG	US-4,962,051	10/09/1990	Liaw, H. M.	11/18/1988
TAG	US-5,735,949	04/07/1998	Manti, S., et al.	09/13/1991
-344	US-6,825,102	11/30/2004	Bedell, S. W., et al.	09/18/2003

FOREIGN PATENT DOCUMENTS				
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T²

	OTHE	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T
JAG		KAL, S., et al., "Strained Silicon-SiGe Devices Using Germanium Implantation", IETE Journal of Research, 43 (2-3), (Mar. 1997), 185-192	
Th		XIAO, Q., et al., "Preparation of thin Strained Si Film by Low Temperature Ge lon Implantation and High Temperature Annealing", Solid-State and Integrated Circuits Technology, 2004. Proceedings 7th Int'l Conf., 3(3), (Oct. 18, 2004), 2163-2166	

EXAMINER

DATE CONSIDERED

PTO/SB/CBA(10-01)
Approved for use through 10/31/2002, OMB 651-0031
US Paleat & Tradement Other U.B. DEPARTMENT OF COMMERCE
On of Information Unions & providing a serial ASS

Substitute for form 1449A/PTO
INFORMATION DISCLOSURE
STATEMENT BY APPLICANT
(Use as many sheets as necessary)

Application Number	10/634,174		
Filing Date	August 5, 2003		
First Named Inventor	Forbes, Leonard		
Group Art Unit	2823		
Examiner Name	Garcia, Joannie		

Sheet	4	-4	4	
DHEBL	ł	П	1	
		•	•	

		US PATE	NT DOCUMENTS	
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date if Appropriate
JAG	US-2004/0171196-A1	09/02/2004	Walitzki, H J.	08/07/2003
JAC	US-2004/0173798	09/09/2004	Forbes, Leonard	03/05/2003
JAC	US-2004/0214366-A1	10/28/2004	Segal, B M., et al.	05/20/2004
145	US-2004/0217352-A1	11/04/2004	Forbes, L.	04/29/2003
JAC	US-2004/0217391	11/04/2004	Forbes, Leonard	04/29/2003
JAC	US-2004/0224480-A1	11/11/2004	Forbes, L.	05/07/2003
JA	US-2004/0232422-A1	11/25/2004	Forbes, L.	05/21/2003
JKS.	US-2004/0232487-A1	11/25/2004	Forbes, L.	05/21/2003
SAG	US-2004/0232488-A1	11/25/2004	Forbes, L.	05/21/2003
SAC	US-2004/0235264-A1	11/25/2004	Forbes, L.	05/21/2003
SK	US-2005/0017273-A1	01/27/2005	Forbes, L., et al.	07/21/2003
JAC	US-2005/0020094-A1	01/27/2005	Forbes, L., et al.	07/21/2003
JK.	US-2005/0023529-A1	02/03/2005	Forbes, L.	08/31/2005
145	US-2005/0023612-A1	02/03/2005	Forbes, L.	08/31/2004
314	US-2005/0023616-A1	02/03/2005	Forbes, L.	08/31/2004
SAC	US-2005/0029683-A1	02/10/2005	Forbes, L., et al.	08/31/2004
JAC	US-2005/0032296-A1	02/10/2005	Forbes, L.	08/31/2004
JAG	US-4,523,975	06/18/1985	Groves, C. K., et al.	04/28/1982
JAG	US-5,854,501	12/29/1998	Kao, D. Y.	11/20/1995
DAG.	US-5,877,070	03/02/1999	Goesele, U. M., et al.	05/31/1997
JK	US-5,987,200	11/16/1999	Fleming, D. A., et al.	10/27/1997
SAC	US-6,103,598	08/15/2000	Yamagata, K., et al.	07/11/1996
JAC	US-6,143,628	11/07/2000	Sato, N., et al.	03/25/1998
JK	US-6,162,657	12/19/2000	Schiele, I., et al.	05/11/1999
ONG	US-6,180,487	01/30/2001	Lin, M.	10/25/1999
OKA	US-6,328,796	12/11/2001	Kub, F. J., et al.	02/01/1999
JAC	US-6,455,397	09/24/2002	Belford, Rona E.	11/09/2000
JAC	US-6,486,008	11/26/2002	Lee, T.	08/01/2000
DK	US-6,497,763	12/24/2002	Kub, F. J., et al.	01/19/2001
AC	US-6,514,836	02/04/2003	Belford, Rona E.	06/04/2001
144	US-6,656,822	12/02/2003	Doyle, B. S., et al.	06/28/1999
M	US-6,689,671	02/10/2004	Yu, B, et al.	05/22/2002
SKG.	US-6,812,508	11/02/2004	Fukumi, M.	11/27/2001

	OTHE	R DOCUMENTS - NON PATENT LITERATURE DOCUMENTS	
Examiner initials*	Cite No 1	(book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	7
JK		LU, X., et al., "SiGe and SiGeC Surface Alloy Formation Using High-Dose Implantation and Solid Phase Epitaxy", Proceedings of the 11th International Conference on Ion Implantation Technology, Austin, TX, (1997), 686-689	

EXAMINER	ogmet Dancis

DATE CONSIDERED September 29,2005